

L Number	Hits	Search Text	DB	Time stamp
1	5	taalo altao	USPAT; US-PGPUB	2003/01/02 07:51
2	9	"AlTaO.sub.4"	USPAT; US-PGPUB	2003/01/02 07:51
3	0	"(ABO.sub.4).sub.x(M.sub.nO.sub.m).sub.1-x"	USPAT; US-PGPUB	2003/01/02 07:52
4	0	"(ABO.sub.4).sub.x (M.sub.nO.sub.m).sub.1-x"	USPAT; US-PGPUB	2003/01/02 07:52
5	0	"(ABO.sub.4).sub.x(M.sub.nO.sub.m).sub.1-x"	USPAT; US-PGPUB	2003/01/02 07:52
6	19	"ABO.sub.4"	USPAT; US-PGPUB	2003/01/02 07:52
7	21	abo same oxide	USPAT; US-PGPUB	2003/01/02 07:53
8	0	"--(ABO.sub.4).sub.x(M.sub.nO.sub.m).sub.1-x--"	USPAT; US-PGPUB	2003/01/02 07:53
9	18	abo same gate	USPAT; US-PGPUB	2003/01/02 07:53
10	79	(abo and transistor) not (abo adj et)	USPAT; US-PGPUB	2003/01/02 07:54
11	0	"AlTaO.sub.4"	EPO; JPO; DERWENT; IBM_TDB	2003/01/02 07:55
12	0	"ABO.sub.4"	EPO; JPO; DERWENT; IBM_TDB	2003/01/02 07:55
13	6	abo and transistor	EPO; JPO; DERWENT; IBM_TDB	2003/01/02 07:55
14	0	((257/410).CCLS.) and abo	USPAT; US-PGPUB	2003/01/02 07:55
15	11	((257/410).CCLS.) and (noncrystalline (non adj crystalline))	USPAT; US-PGPUB	2003/01/02 07:57
16	1	"alo.sub.2" same gate	USPAT; US-PGPUB	2003/01/02 07:59
17	16	"alo.sub.2" and transistor	USPAT; US-PGPUB	2003/01/02 08:00
18	255	(abo and oxide) not (abo adj et)	EPO; JPO; DERWENT; IBM_TDB	2003/01/02 08:04
19	0	((abo and oxide) not (abo adj et)) not aboe	EPO; JPO; DERWENT; IBM_TDB	2003/01/02 08:04
20	0	"--(AlO.sub.2 ).sub.j(M.sub.nO.sub.m).sub.k--"	USPAT; US-PGPUB	2003/01/02 08:05
21	0	"(AlO.sub.2 ).sub.j" adj "(M.sub.n" adj "O.sub.m).sub.k"	USPAT; US-PGPUB	2003/01/02 08:05
22	113	almo	USPAT; US-PGPUB	2003/01/02 08:07
23	7	alomo	USPAT; US-PGPUB	2003/01/02 08:08
24	0	"(AlO.sub.2 ).sub.j" adj "(M.sub.nO.sub.m).sub.k"	USPAT; US-PGPUB	2003/01/02 08:08
25	0	"(AlO.sub.2 ).sub.j" adj "(M.sub.n" adj "O.sub.m).sub.k"	USPAT; US-PGPUB	2003/01/02 08:09
26	19	((yttrium near oxide) (lanthanum near oxide)) same transistor	USPAT; US-PGPUB	2003/01/02 08:09
27	42	((yttrium near oxide) (lanthanum near oxide)) same gate	USPAT; US-PGPUB	2003/01/02 08:12
28	21	(substrate near (gaalas ingaas)) same (transistor gate)	USPAT; US-PGPUB	2003/01/02 08:13
29	0	"(AlTaO.sub.4).sub.x(Hf.sub.nO.sub.m).sub.1-x"	USPAT; US-PGPUB	2003/01/02 08:16

30	0	"(AlTaO.sub.4).sub.x(zr.sub.nO.sub.m).sub.1-x"	USPAT; US-PGPUB	2003/01/02 08:17
31	0	"(AlTaO.sub.4).sub.x(Y.sub.nO.sub.m).sub.1-x"	USPAT; US-PGPUB	2003/01/02 08:17
32	0	"(AlTaO.sub.4).sub.x(La.sub.nO.sub.m).sub.1-x"	USPAT; US-PGPUB	2003/01/02 08:18
33	4310	al with ta with (hf zr y la)	USPAT; US-PGPUB	2003/01/02 08:20
34	1330	(al with ta with (hf zr y la)) same oxide	USPAT; US-PGPUB	2003/01/02 08:19
35	920	(al with ta with (hf zr y la)) with oxide	USPAT; US-PGPUB	2003/01/02 08:22
36	1424	al near5 ta near5 (hf zr y la)	USPAT; US-PGPUB	2003/01/02 08:20
37	361	(al near5 ta near5 (hf zr y la)) with oxide	USPAT; US-PGPUB	2003/01/02 08:20
38	267	(al with ta with (hf zr y la)) with formula	USPAT; US-PGPUB	2003/01/02 08:25
39	1	((al with ta with (hf zr y la)) with formula) same (gate transistor)	USPAT; US-PGPUB	2003/01/02 08:26
40	78	((al with ta with (hf zr y la)) with formula) same oxide	USPAT; US-PGPUB	2003/01/02 08:26